PTO-1449	Application No.	Applicant(s)	
Information Disclosure Citation in an Application	09/864,714	Ajit P. Paranjpe et al.	
	Docket Number	Group Art Unit	Filing Date
	021208.0238	2814	May 23, 2001

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		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	A.	6174377	1/16/2001	Doering et al.	118	729	1/4/99
	B.	5879459	3/09/1999	Gadgil et al.	118	715	8/29/97
	C.	5916365	6/29/1999	Sherman	117	92	8/16/96
	D.	6015590	1/18/2000	Suntola et al.	427	255.23	09/25/96
	E.	6200893	3/13/2001	Sneh	438	685	3/11/99
	F.	6342277	1/29/2002	Sherman	427	562	4/14/99
	G.	2002/0041931	4/11/2002	Suntola et al.	427	255.28	5/14/01
	H.	6387185	5/14/2002	Doering et al.	118	729	1/16/01
	I.	6391785	5/21/2002	Satta et al.	438	704	8/23/00
	J.	6416577	7/9/2002	Suntola et al.	117	88	06/07/00
	K.	2002/0106846	8/8/2002	Seutter et al.	438	200	2/2/01
	L.	2002/0108570	8/15/2002	Lindfors	118	715	4/16/01
	M.	6447607	9/10/2002	Soininen et al.	117	200	12/27/00
	N.	6451119*	9/17/2002	Sneh et al.	118	715	11/29/00
	O.	6451695	9/17/2002	Sneh	438	685	12/22/00
	P.	6464779	10/15/2002	Powell et al.	117	89	1/19/01
	Q.	6475910	11/5/2002	Sneh	438	685	9/22/00
	R.	6475276	11/5/2002	Elers et al.	117	84	10/13/00
	S.	6482262	11/19/2002	Elers et al.	117	84	10/13/00
	T.	6482740	11/19/2002	Soininen et al.	438	686	5/15/01

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	U.	62221102	09/29/1987	JP (with English abstract)	H01F	41/14		X
	V.	WO 00/38191	06/29/2000	PCT	G11C	11/15	X	

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	X.	Akerman, J.J et al., "Identifying Tunneling in Ferromagnetic-Insulator-Ferromagnetic Thin Film Structures", World-wide web, physics.ucsd.edu/ksgrp/Tunneling.html, pp. 1-6,	Printed 02/04/2002
	Y.	Bobo, J.F. et al., "Spin-dependent Tunneling Junctions with Hard Magnetic layer Pinning", *Journal of Applied Physics*, vol. 83, No. 11, pp. 6685-6687	1998
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	A.	2002/0187084	12/12/2002	Lindfors et al.	422	177	7/24/02
	B.	6503330	1/7/2003	Sneh et al.	118	715	12/22/99
	C.	6506352	1/14/2003	Lindfors et al.	423	240	7/20/00
	D.	6511539	1/28/2003	Raaijmakers	117	102	9/8/99
	E.	6524952	2/25/2003	Srinivas et al.	438	649	6/20/00
	F.	6540838	4/1/2003	Sneh et al.	118	715	6/28/02
	G.	6548424	4/15/2003	Putkonen	438	785	4/16/01
	H.	6551406	4/22/2003	Kilpi	118	728	12/27/00
	I.	6562140	5/13/2003	Bondestam et al.	118	715	5/10/00
	J.	2003/0096468	5/22/2003	Soininen et al.	438	200	11/19/02
	K.	6572705	6/3/2003	Suntola et al.	118	702	1/14/00
	L.	2003/0101927	6/5/2003	Raaijmakers	117	200	12/10/02
	M.	6579374	6/17/2003	Bondestam et al.	118	725	1/25/01
	N.	2003/0121469	7/3/2003	Lindfors et al.	117	105	10/11/02
	O.	6599572	7/29/2003	Saanila et al.	427	249.18	1/18/01
	P.	2003/0140854	7/31/2003	Kilpi	118	715	2/13/03
	Q.	6602784	8/5/2003	Sneh	438	680	8/6/02
	R.	2003/0150385	8/14/2003	Bondestam et al.	118	722	3/6/03
	S.	6616986	9/9/2003	Sherman	427	562	10/9/01
	T.	6620723	9/16/2003	Byun et al.	438	627	6/27/00
	U.	6627268	9/30/2003	Fair et al.	427	533	5/3/01

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	Y.	Hsaio, R., "Fabrication of Magnetic Recording Heads and Dry Etching Head Materials", IBM Journal of Research and Development, vol. 43, (1/2):1999, pp. 89-102	1999
	Z.	Imai, Takuji, World-wide web nikkeibp.asiabiztech.com/nea/200008/tech_108675.html, "100 Gbit/inch HDD Just Around the Corner", pp. 1-6	08/2000

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SR	A.	2003/0183171	10/2/2003	Sneh et al.	118	724	3/27/03
	B.	6630401	10/7/2003	Sneh	438	680	8/6/02
	C.	6630030	10/7/2003	Suntola et al.	118	728	1/4/00
	D.	6632279	10/14/2003	Ritala et al.	117	101	10/13/00
	E.	6635965	10/21/2003	Lee et al.	257	758	10/9/01
	F.	6638862	10/28/2003	Sneh	438	685	8/6/02
	G.	6638859	10/28/2003	Sneh et al.	438	680	9/27/02
	H.	6638810	10/28/2003	Baklı et al.	438	240	11/5/01
	I.	6652924	11/25/2003	Sherman	427	576	5/24/01
	J.	6660126	12/9/2003	Nguyen et al.	156	345.34	3/2/01
	K.	6664192	12/16/2003	Satta et al.	438	704	4/15/02
	L.	2004/0005753	1/8/2004	Kostamo et al.	438	222	3/20/03
	M.	2004/0007171	1/15/2004	Ritala et al.	117	89	7/10/03
	N.	6679951	1/20/2004	Soininen et al.	148	240	11/13/01
	O.	6689210	2/10/2004	Soininen et al.	117	89	7/24/02
	P.	6720260	4/13/2004	Fair et al.	438	680	6/20/03
	Q.	2004/0076837	4/22/2004	Hein et al.	428	446	10/22/02
	R.	2004/0076751	4/22/2004	Sherman	427	255.34	10/10/03
	S.	6727169	4/27/2004	Raaijmakers et al.	438	622	8/23/00
	T.	2004/0083949	5/6/2004	Sherman	117	84	10/22/03
	U.	6734020	5/11/2004	Lu et al.	436	55	3/7/01
	V.	2004/0121616	6/24/2004	Satta et al.	438	778	12/8/03
	W.	6759081	7/6/2004	Huganen et al.	427	58	4/30/02
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	A.	6764546	7/20/2004	Raaijmakers	117	93	12/10/02
	B.	6767582	7/27/2004	Elers	427	253	10/12/00
	C.	6777353	8/17/2004	Putkonen	438	785	4/8/03
	D.	2004/0161636	8/19/2004	Hujanen et al.	428	692	2/17/04
	E.	6784287	9/21/2004	Saanila et al.	438	674	3/20/03
	F.	6800173	10/5/2004	Chiang et al.	156	345.33	7/9/01
	G.	6800552	10/5/2004	Elers et al.	438	680	9/17/02
	H.	2004/0202786	10/14/2004	Wongsenakhum et al.	427	250	3/31/04
	I.	6811814	11/2/2004	Chen et al.	427	248.1	1/16/02
	J.	6818067	11/16/2004	Doering et al.	118	715	4/15/02
	K.	6821889	11/23/2004	Elers et al.	438	680	7/30/02

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	N.	Riihela et al., "Low Temperature Deposition of AlN Films by an Alternate Syppy of Trimethyl Aluminum and Ammonia" Chemical Vapor Deposition, 2 (6): pp. 277-283.	1996
	O.	Suntola, Tuomo; *Handbook of Crystal Growth*, vol. 3, Thin Films and Epitaxy, Part B: Growth Mechanisms and Dynamics, Chapter 14, pp. 601-663, Hurle, ed. Elsevier Science B.V.	1994
	P.	Ritala et al., "Ataomic Layer Epitaxy-a Valuable Tool for Nanotechnology?" Nanotechnology vol. 10, pages 19-24	1999
	Q.	Wang, Shan X., "Advanced Materials for Extremely High Density Magnetic Reocrding Heads," Department of Electrical Engineering, Stanford University, Stanford, CA 94305-4045, presentation.	no date available
	R.	World-wide web, megahaus.com/tech/westerndigital/shitepapers/gmr_wp.shtml., "GMR Head Technology: Increased Areal Density and Improved Performance Areal Density," pp. 1-4.	02/2000
	S.	World-wide web, semiconductor.net/semiconductor/issues/issues/1998/feb98/docs/emerging.asp, "GMR Read-Write Heads Yield Data Storage Record," pp. 1-2.	02/1998
	T.	World-wide web, stoner.leeds.ac.uk/research/gmr.htm, "Giant Magnetoresistance (GMR) Heads", pp. 1-6.	Printed 02/04/2002
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	A.	Utriainen, et al., "Studies of Metallic Film Growth in an Atomic Layer Epitaxy reactor Using M(acac)2(M=Ni, Cu, Pt) Precursors", Applied Surface Science, vol. 157, pp. 151-158.	2000
	V.	Ueno et al., "Cleaning of CHF3, plasma-etched SiO2/SiN/CU via Structures Using a Hydrogen Plasma, an Oxygen Plasma and Hexafluoroacetylacetone Vapors," *J. VAc. Sci. Technology B*, vol. 16, No. 6, pp. 2986-2995.	Nov./Dec. 1998

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	A.	5647911	07/15/97	Vanell et al.	118	715	12/14/93
	B.	5711811	01/27/98	Suntola et al.	118	711	11/28/95
	C.	5916369	06/29/99	Anderson et al.	118	715	06/07/95
	D.	2003/0003635 A1	01/02/03	Paranjpe et al.	438	149	05/23/01
	E.						
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	M.		
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